

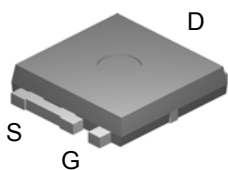
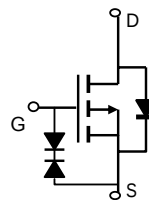
**AOL1401****P-Channel Enhancement Mode Field Effect Transistor****General Description**

The AOL1401 uses advanced trench technology to provide excellent $R_{DS(ON)}$, and ultra-low low gate charge with a 25V gate rating. This device is suitable for use as a load switch or in PWM applications. It is ESD protected. *Standard Product AOL1401 is Pb-free (meets ROHS & Sony 259 specifications). AOL1401L is a Green Product ordering option. AOL1401 and AOL1401L are electrically identical.*

Features
 $V_{DS} (V) = -38V$
 $I_D = -85A$
 $R_{DS(ON)} < 8.5m\Omega (V_{GS} = -10V)$
 $R_{DS(ON)} < 10m\Omega (V_{GS} = -4.5V)$

ESD Rating: 3000V HBM

Ultra SO-8™ Top View

Fits SOIC8 footprint !
 Bottom tab
connected to
drain
**Absolute Maximum Ratings** $T_A=25^\circ\text{C}$ unless otherwise noted

Parameter	Symbol	Maximum	Units
Drain-Source Voltage	V_{DS}	-38	V
Gate-Source Voltage	V_{GS}	± 25	V
Continuous Drain Current ^G	I_D	-85	A
$T_C=25^\circ\text{C}$		-62	
$T_C=100^\circ\text{C}$	I_{DSM}	-120	
Pulsed Drain Current ^C		-12	
Continuous Drain Current ^G	P_D	100	W
$T_A=25^\circ\text{C}$		50	
$T_A=70^\circ\text{C}$	P_{DSM}	2.1	W
Power Dissipation ^B		1.3	
Power Dissipation ^A	T_J, T_{STG}	-55 to 175	$^\circ\text{C}$

Thermal Characteristics

Parameter	Symbol	Typ	Max	Units
Maximum Junction-to-Ambient ^A	$R_{\theta JA}$	21	25	$^\circ\text{C/W}$
$t \leq 10s$		48	60	$^\circ\text{C/W}$
Maximum Junction-to-Ambient ^A	$R_{\theta JC}$	1	1.5	$^\circ\text{C/W}$
Steady-State				

Electrical Characteristics ($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	$I_D=-250\mu\text{A}$, $V_{GS}=0\text{V}$	-38			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-30\text{V}$, $V_{GS}=0\text{V}$ $T_J=55^{\circ}\text{C}$			-100 -500	nA
I_{GSS}	Gate-Body leakage current	$V_{DS}=0\text{V}$, $V_{GS}=\pm 20\text{V}$			± 1	μA
		$V_{DS}=0\text{V}$, $V_{GS}=\pm 25\text{V}$			± 10	μA
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=-250\mu\text{A}$	-1.5	-2.2	-3.5	V
$I_{D(ON)}$	On state drain current	$V_{GS}=-10\text{V}$, $V_{DS}=-5\text{V}$	-120			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=-20\text{V}$, $I_D=-20\text{A}$ $T_J=125^{\circ}\text{C}$		6.8 9.1	8.5 11	$\text{m}\Omega$
		$V_{GS}=-10\text{V}$, $I_D=-20\text{A}$		7.9	10	$\text{m}\Omega$
g_{FS}	Forward Transconductance	$V_{DS}=-5\text{V}$, $I_D=-20\text{A}$		50		S
V_{SD}	Diode Forward Voltage	$I_S=-1\text{A}$, $V_{GS}=0\text{V}$		0.71	-1	V
I_S	Maximum Body-Diode Continuous Current				14.5	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	$V_{GS}=0\text{V}$, $V_{DS}=-20\text{V}$, $f=1\text{MHz}$		3800	4560	pF
C_{oss}	Output Capacitance			560		pF
C_{rss}	Reverse Transfer Capacitance			350		pF
R_g	Gate resistance	$V_{GS}=0\text{V}$, $V_{DS}=0\text{V}$, $f=1\text{MHz}$		7.5	9	Ω
SWITCHING PARAMETERS						
$Q_g(10\text{V})$	Total Gate Charge (10V)	$V_{GS}=-10\text{V}$, $V_{DS}=-20\text{V}$, $I_D=-20\text{A}$		61.2	74	nC
$Q_g(4.5\text{V})$	Total Gate Charge (4.5V)			30.8	37	nC
Q_{gs}	Gate Source Charge			11.88		nC
Q_{gd}	Gate Drain Charge			15.4		nC
$t_{D(on)}$	Turn-On DelayTime	$V_{GS}=-10\text{V}$, $V_{DS}=-20\text{V}$, $R_L=1\Omega$, $R_{GEN}=3\Omega$		13.5		ns
t_r	Turn-On Rise Time			17		ns
$t_{D(off)}$	Turn-Off DelayTime			97		ns
t_f	Turn-Off Fall Time			43		ns
t_{rr}	Body Diode Reverse Recovery Time	$I_F=-20\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		30	36	ns
Q_{rr}	Body Diode Reverse Recovery Charge	$I_F=-20\text{A}$, $dI/dt=100\text{A}/\mu\text{s}$		29		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$. The Power dissipation P_{DSM} is based on $R_{\theta JA}$ and the maximum allowed junction temperature of 150°C . The value in any given application depends on the user's specific board design, and the maximum temperature of 175°C may be used if the PCB allows it.

B: The power dissipation P_D is based on $T_{J(MAX)}=175^{\circ}\text{C}$, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C: Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=175^{\circ}\text{C}$.

D: The $R_{\theta JA}$ is the sum of the thermal impedance from junction to case $R_{\theta JC}$ and case to ambient.

E: The static characteristics in Figures 1 to 6 are obtained using $<300\mu\text{s}$ pulses, duty cycle 0.5% max.

F: These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of $T_{J(MAX)}=175^{\circ}\text{C}$.

G: The maximum current rating is limited by bond-wires.

H: These tests are performed with the device mounted on 1 in 2 FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^{\circ}\text{C}$.

Rev 0: September 2005

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

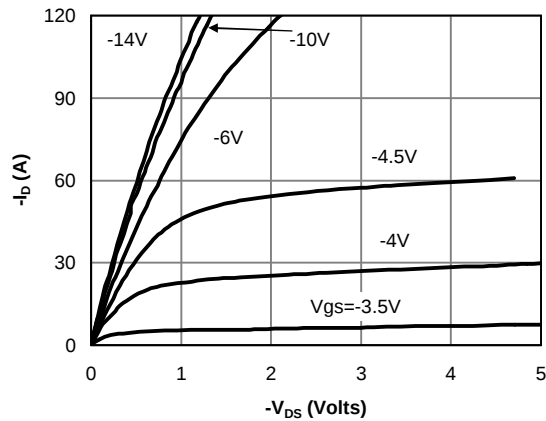


Fig 1: On-Region Characteristics

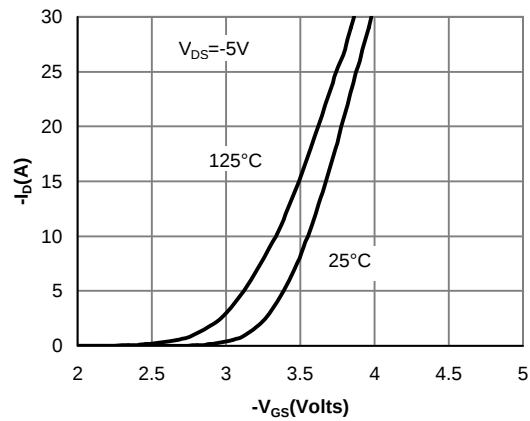


Figure 2: Transfer Characteristics

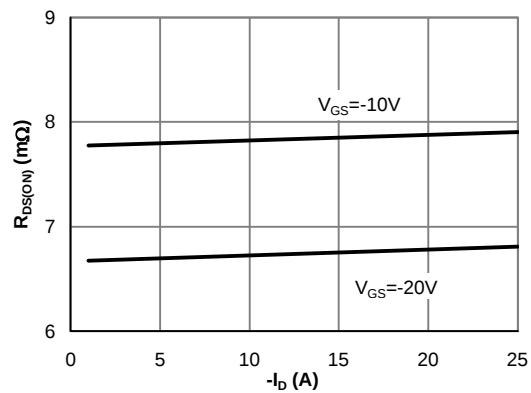


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

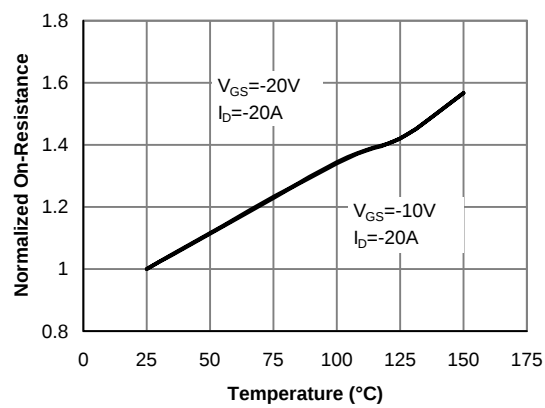


Figure 4: On-Resistance vs. Junction Temperature

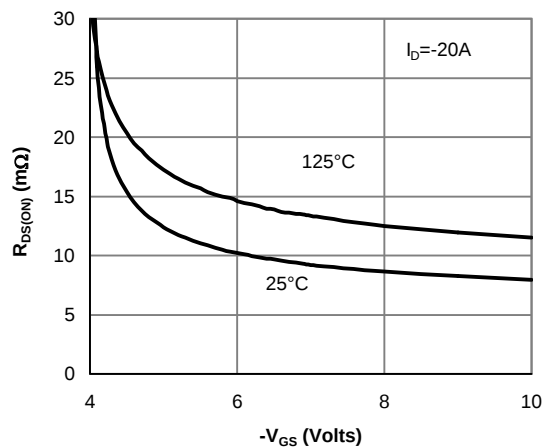


Figure 5: On-Resistance vs. Gate-Source Voltage

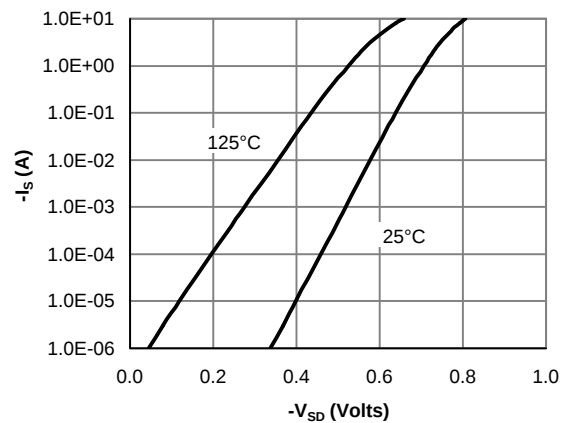


Figure 6: Body-Diode Characteristics

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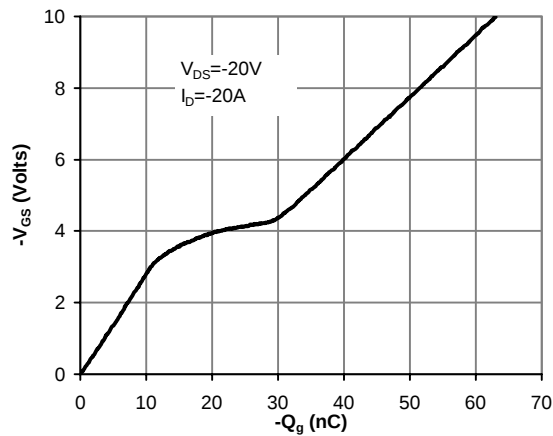


Figure 7: Gate-Charge Characteristics

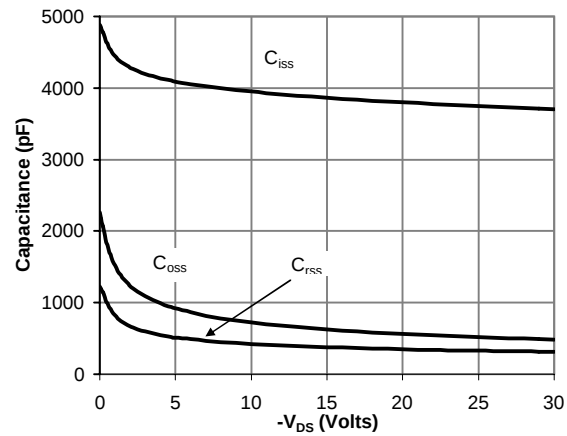


Figure 8: Capacitance Characteristics

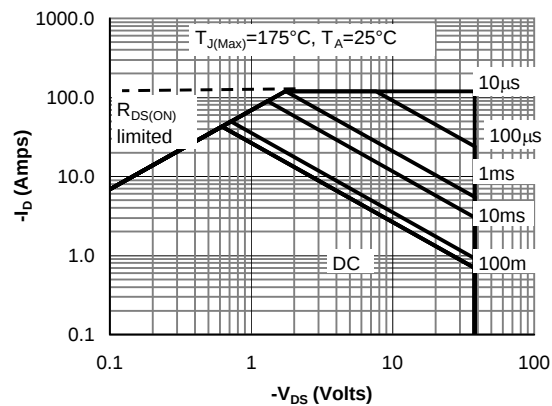


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

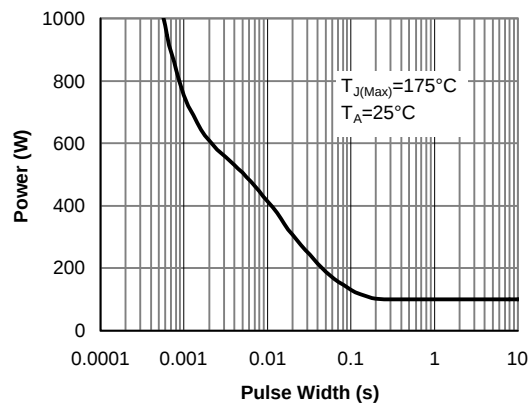


Figure 10: Single Pulse Power Rating Junction-to-Case (Note B)

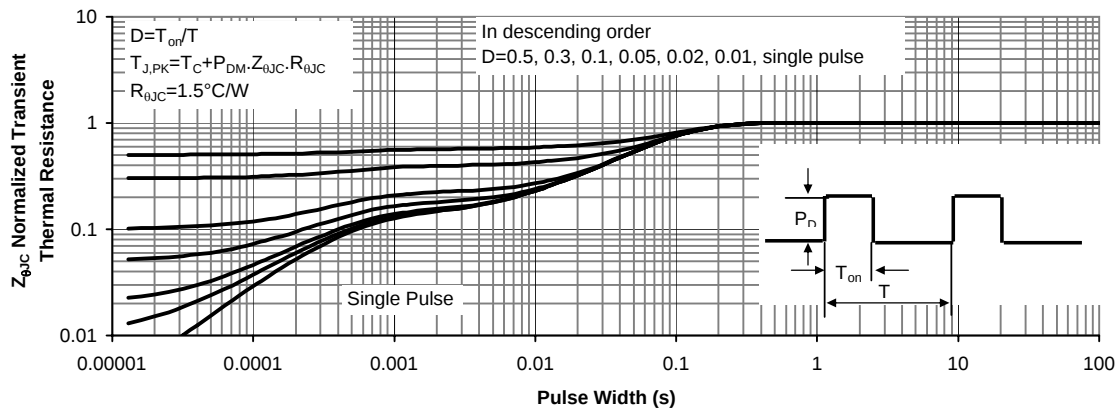


Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

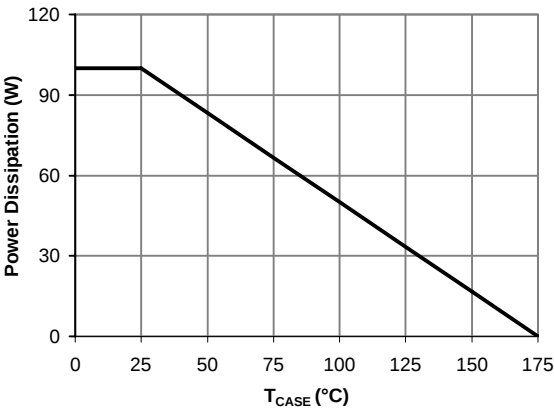


Figure 12: Power De-rating (Note B)

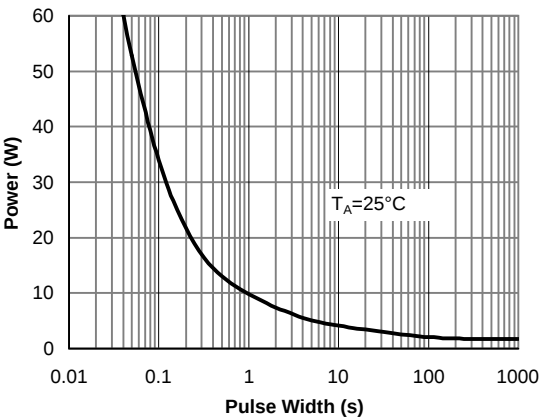


Figure 13: Single Pulse Power Rating Junction-to-Ambient (Note H)

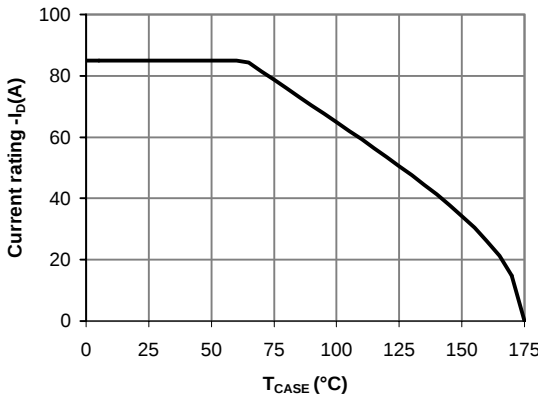


Figure 14: Current De-rating (Note B)

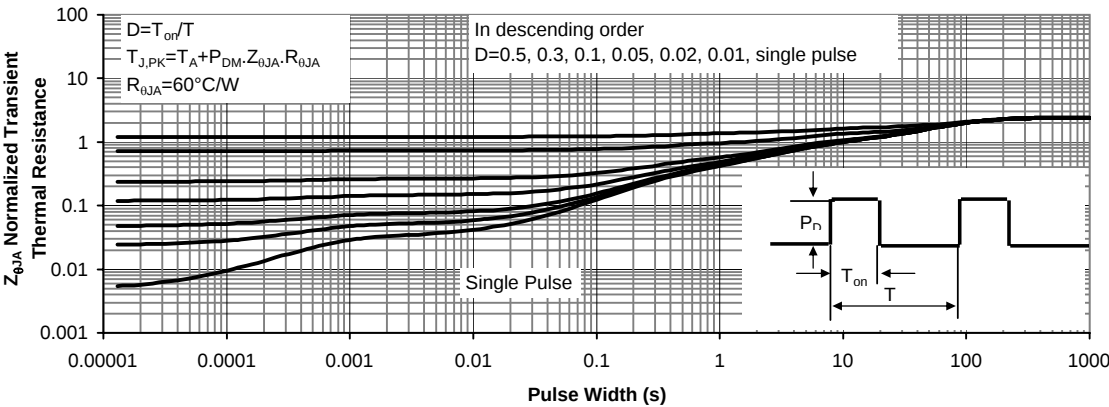


Figure 15: Normalized Maximum Transient Thermal Impedance (Note H)